10/593878

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Katsunori ASANO et al. Atty. Ref.: 925-354

Serial No. To be assigned TC/A.U.: To be assigned

Filed: September 22, 2006 Examiner: To be assigned

For: VOLTAGE-CONTROLLED SEMICONDUCTOR DEVICE

September 22, 2006

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. Copies of the International Search Report and cited references are attached.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By:

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IAP16 Rec'd PCT/PTO 22 SEP 2006 PTO/SB/08a

INFORMATION	DISCLOSURE
CITAT	ION

ATTY. DOCKET NO.

925-354

APPLICANT

Katsunori ASANO et al.

(Use several sheets if necessary)

FILING DATE

TC/A.U.

September 22, 2006

To be assigned

INITIAL	DOCUMENT NUMBER	DATE		OCUMENTS NAME	CLASS	SUBCLASS	FILING IF APPRO	DATE
	5,917,204	6/1999	Bh	atnagar et al.	02/100		<u> </u>	
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	DOCUMENT	DATE		COUNTRY	CLASS	SUBCLASS	YES	NO
	2003-31802	1/2003		Japan			ABSTRACT	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.